

Title (en)  
Combined precharge and equalisation circuit

Title (de)  
Kombinierte Vorlade- und Homogenisierschaltung

Title (fr)  
Circuit de précharge et d'égalisation

Publication  
**EP 0980074 B1 20050615 (DE)**

Application  
**EP 99115517 A 19990805**

Priority  
DE 19836736 A 19980813

Abstract (en)  
[origin: DE19836736C1] Combined precharging- and homogenisation circuit includes first and second FET type precharging transistors (1,3) and a homogenisation (equalising) transistor (2) connected in series between the two precharging transistors. The common gate (11,12) arrangement is an angled structure turned through approx. 45 deg. relative to the bit lines length (BLT,BLC). The common drain (7,10) and the common source/drain (8,9) are brought out over the common gate (11,12) and have zones jutting out, with the bit line contacts (15) located in these salient zones.

IPC 1-7  
**G11C 7/12**

IPC 8 full level  
**G11C 7/12** (2006.01); **H10B 12/00** (2023.01)

CPC (source: EP KR US)  
**G11C 7/12** (2013.01 - EP US); **G11C 11/40** (2013.01 - KR); **H10B 12/00** (2023.02 - EP US)

Designated contracting state (EPC)  
DE FR GB IE IT

DOCDB simple family (publication)  
**DE 19836736 C1 19991230**; DE 59912177 D1 20050721; EP 0980074 A1 20000216; EP 0980074 B1 20050615; JP 2000068470 A 20000303; JP 3512684 B2 20040331; KR 100310519 B1 20011018; KR 20000017242 A 20000325; TW 519659 B 20030201; US 6081469 A 20000627

DOCDB simple family (application)  
**DE 19836736 A 19980813**; DE 59912177 T 19990805; EP 99115517 A 19990805; JP 22774799 A 19990811; KR 19990032865 A 19990811; TW 88113728 A 19990811; US 37489499 A 19990813